

L Number	Hits	Search Text	DB	Time stamp
1	1832	field adj emission adj cathode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 11:29
2	25	field adj emission adj cathode and gate and (field adj effect adj transistor or fet) and source and drain and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 11:39
6	174	(cold adj cathode or field adj emission adj cathode) and 257/\$7.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 11:53
7	135	(cold adj cathode or field adj emission adj cathode and extraction adj gate) and 257/\$7.ccls.	USPAT	2002/05/19 11:53
8	135	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel) and 257/\$7.ccls.	USPAT	2002/05/19 12:04
9	0	cold adj cathode and field adj emission adj (display or cathode) and extraction adj gate and channel and 257/\$7.ccls.	USPAT	2002/05/19 11:59
10	1046	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel) and 313/\$7.ccls.	USPAT	2002/05/19 12:05
11	1045	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel and silicon adj substrate) and 313/\$7.ccls.	USPAT	2002/05/19 12:06
12	1045	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet)) and 313/\$7.ccls.	USPAT	2002/05/19 12:27
13	634	(cold adj cathode or field adj emission adj cathode and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet)) and 315/\$7.ccls.	USPAT	2002/05/19 12:28
14	1	(cold adj cathode or field adj emission adj cathode) and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet) and 315/\$7.ccls.	USPAT	2002/05/19 12:28
15	0	(cold adj cathode or field adj emission adj cathode) and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet) and 313/\$7.ccls.	USPAT	2002/05/19 12:29
16	1	(cold adj cathode or field adj emission adj cathode) and extraction adj gate and channel and silicon adj substrate and (field adj effect adj transistor or fet) and (313/\$7.ccls. or 315/\$6.ccls. or 257/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:30

17	34	(US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.	USPAT; JPO; DERWENT	2002/05/19 12:40
18	14	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and (p-type or p adj type or p-silicon or p-doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:37
19	2	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and (p-type or p adj type or p-silicon or p-doped)) and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:37

20	8	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and focus\$4	USPAT; JPO; DERWENT	2002/05/19 12:43
22	2	((US-5142184-\$ or US-5191217-\$ or US-5212426-\$ or US-5229331-\$ or US-5633560-\$ or US-6075315-\$ or US-6181060-\$ or US-6211608-\$ or US-6340859-\$ or US-6351059-\$ or US-6356014-\$ or US-6369496-\$ or US-6369505-\$ or US-5285079-\$ or US-5319233-\$ or US-5550426-\$ or US-5844252-\$ or US-5910701-\$ or US-6031250-\$ or US-6031322-\$ or US-6084341-\$ or US-6218771-\$ or US-6140701-\$ or US-5500572-\$ or US-5007873-\$ or US-5012482-\$).did. or (US-5055077-\$).did. or (JP-10074473-\$ or JP-09063467-\$ or JP-09063466-\$ or JP-11102637-\$ or JP-09035622-\$ or JP-09259746-\$).did. or (EP-651417-\$).did.) and focus\$4	USPAT; JPO; DERWENT	2002/05/19 12:45
23	0	cold adj cathode and (fet or field adj effect adj transistor) and field adj emission and extract\$3 near4 gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; JPO; DERWENT	2002/05/19 12:48
24	0	cold adj cathode and (fet or field adj effect adj transistor) and field adj emission and extract\$3 near4 gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:49
25	0	cold adj cathode and field adj emission and extract\$3 near4 gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:49
26	13	(cold near2 cathode or field adj emission adj cathode) and gate and source and drain and channel and silicon near4 substrate and (ldd or lightly-doped or lightly adj doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:53
27	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 12:59
28	6952	lightly adj doped adj drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:02

29	2155	lightly adj doped adj drain.ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:15
30	0	lightly adj doped adj drain.ti,ab. and cold adj cathode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:03
31	0	lightly adj doped adj drain.ti,ab. and field adj emission adj cathode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:04
32	0	(ldd or lightly-doped adj drain or lightly adj doped adj drain) and (cold adj cathode or field adj emission adj cathode).ti,ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:08
33	0	jp-6055616\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:11
34	2	jp-60055616\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:11
35	1	lightly adj doped adj drain.ti,ab. and phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:17
36	0	lightly adj doped adj drain near10 phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:17
37	0	(ldd or lightly adj doped adj drain) near10 phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:18
38	1	(ldd or lightly adj doped adj drain) and phosphorus near10 arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 13:27
40	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:07
41	1750	ldd and phosphorus same arsenic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:08
42	16	ldd and phosphorus same arsenic same different near3 diffusion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:09
47	0	cold adj cathode and (field adj effect adj transistor or fet) and (gate near4 different near4 width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:58

48	200	(field adj effect adj transistor or fet) and (gate near4 different near4 width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 14:59
50	2	(field adj effect adj transistor or fet) and (gate near4 different near4 width) and (hot near3 electron) and (ldd or lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:00
49	10	(field adj effect adj transistor or fet) and (gate near4 different near4 width) and (hot near3 electron)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:01
53	1068	width near6 gate near6 (variable or different)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:08
54	137	width near6 gate near6 (variable or different) and 257/\$6.ccls. and (ldd or lightly-doped drain or lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:09
55	90	width near3 gate near3 (variable or different) and 257/\$6.ccls. and (ldd or lightly-doped drain or lightly adj doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:11
56	27	width near3 gate near3 (variable or different) and 257/\$6.ccls. and (ldd or lightly-doped drain or lightly adj doped adj drain) and plan adj view	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:19
57	329	257/249.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:24
58	6	257/249.ccls. and (ldd or lightly adj doped adj drain or lightly-doped adj drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:21
59	15	257/249.ccls. and gate adj width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:29
60	114	257/401.ccls. and gate adj width	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:36
61	13	257/401.ccls. and gate near3 (width or wider) near4 source near4 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 15:43
62	2	jp-60022375\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 16:37
63	2	("5550435").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 16:55

64	1002	shield\$3 near4 gate near4 electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 16:56
65	3849	shield\$3 adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 16:56
66	556	shield\$3 adj electrode and (257/\$6.ccls. or 313/\$6.ccls. or 315/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 16:57
67	3	shield adj electrode near10 gate and (257/\$6.ccls. or 313/\$6.ccls. or 315/\$6.ccls.) and (cold adj cathode or field adj emission)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 17:31
68	2645	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/146) or (257/153)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:36
69	697	(electrode near3 (shield or shielding) near3 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 17:38
70	398	(electrode near3 (shield or shielding) near3 gate) and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 18:26
71	0	(electrode near3 (shield or shielding) near3 gate) and channel and flat adj type adj display	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 18:27
72	13	(electrode near3 (shield or shielding) near3 gate) and channel and flat adj2 display	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 19:57
73	0	jp-0963467\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 20:53
74	2	((("5550435") or ("5396096")).PN.	USPAT	2002/05/19 21:09
75	2	jp-62229880\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:18
76	0	jp-64061953\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:18
77	0	jp-6461953\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:18
78	4003	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/249) or (257/401) or (257/146) or (257/153)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:55

79	12	((315/169.1) or (315/169.2) or (315/167) or (315/309) or (313/336) or (257/249) or (257/401) or (257/146) or (257/153)).CCLS.) and shield near3 electrode near3 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 21:38
80	238	(257/10).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 22:06
81	0	(257/10 and shield\$3).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 22:07
82	18	((257/10).CCLS.) and shield\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/19 22:07
-	0	jp-963467\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/18 20:55
-	0	jp-40963467\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/18 20:56
-	0	"9-63467"	JPO	2002/05/18 20:58
-	0	"963467"	JPO	2002/05/18 20:58
-	0	"963467"\$3	JPO	2002/05/18 20:58
-	4	cold adj electron adj emitting adj element and hirano.in. and ito.in.	JPO	2002/05/18 22:06
-	57881	yamaguchi.in. hirakawa.in. and tomita.in.	JPO	2002/05/18 21:02
-	1	yamaguchi.in. and hirakawa.in. and tomita.in.	JPO	2002/05/18 21:05
-	1	mosfet adj type adj electron adj emission adj element	JPO	2002/05/18 21:06
-	1	jp-07130281\$-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/18 21:36
-	7109	315/\$6.ccls.	JPO	2002/05/18 22:07
-	52381	315/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/05/18 22:07